

### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	40	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Collector Current	lc	200	mA

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	PD	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0JA</sub>	625	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

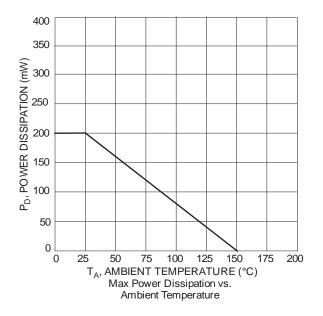
## ESD Ratings (Note 6)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

5. For a device mounted with the collector lead on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is Notes: measured under still air conditions whilst operating in a steady-state. 6. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



# Thermal Characteristics and Derating Information





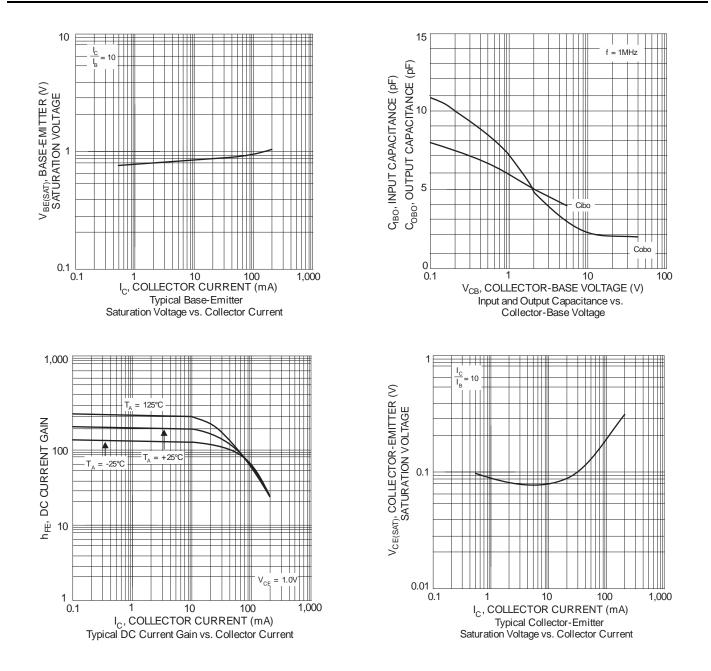
# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)	Cymbol		Шах	•	
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	60		V	$I_{\rm C} = 10 \mu A, I_{\rm E} = 0$
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	40	_	V	$I_{\rm C} = 1 {\rm mA}, I_{\rm B} = 0$
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	5	_	V	$I_{\rm E} = 10\mu A, I_{\rm C} = 0$
Collector Cutoff Current	I <sub>CEX</sub>	_	50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3V$
Base Cutoff Current	I <sub>BL</sub>	_	50	nA	$V_{CE} = 30V, V_{EB(OFF)} = 3V$
ON CHARACTERISTICS (Note 7)					· · · · · · · · · · · · · · · · · · ·
	40 —		$I_{C} = 100 \mu A, V_{CE} = 1 V$		
		70	_		$I_C = 1mA$ , $V_{CE} = 1V$
DC Current Gain	h <sub>FE</sub>	100	300		$I_{C} = 10 \text{mA}, V_{CE} = 1 \text{V}$
		60			$I_{C} = 50 \text{mA}, V_{CE} = 1 \text{V}$
		30			$I_{C} = 100 \text{mA}, V_{CE} = 1 \text{V}$
Collector-Emitter Saturation Voltage	N	_	0.25	V	$I_{C} = 10mA, I_{B} = 1mA$
	V <sub>CE(SAT)</sub>		0.30	v	$I_{C} = 50 \text{mA}, I_{B} = 5 \text{mA}$
Base-Emitter Saturation Voltage	<i>M</i> =====	0.65	0.85	0.85 V	$I_{C} = 10mA, I_{B} = 1mA$
Ğ	V <sub>BE(SAT)</sub>	_	0.95	v	$I_{C} = 50 \text{mA}, I_{B} = 5 \text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C <sub>obo</sub>	—	4	pF	$V_{CB} = 5V$ , f = 1.0MHz, I <sub>E</sub> = 0
Input Capacitance	C <sub>ibo</sub>	_	8	pF	$V_{EB} = 0.5V, f = 1.0MHz, I_{C} = 0$
Input Impedance	h <sub>ie</sub>	1	10	kΩ	
Voltage Feedback Ratio	h <sub>re</sub>	0.5	8.0	x 10 <sup>-4</sup>	$V_{CE} = 10V, I_{C} = 1mA,$
Small Signal Current Gain	h <sub>fe</sub>	100	400		f = 1.0MHz
Output Admittance	h <sub>oe</sub>	1	40	μS	
Current Gain-Bandwidth Product	fT	300	_	MHz	$V_{CE} = 20V, I_C = 10mA,$ f = 100MHz
Noise Figure	NF		5	dB	$V_{CC} = 5V$ , $I_C = 100$ μA, R <sub>S</sub> = 1kΩ, f = 1MHz
SWITCHING CHARACTERISTICS	I				/
Delay Time	t <sub>d</sub>	_	35	ns	$V_{CC} = 3V, I_{C} = 10mA,$
Rise Time	tr	_	35	ns	$V_{BE(OFF)} = -0.5V, I_{B1} = 1mA$
Storage Time	ts	_	200	ns	$V_{CC} = 3.0V, I_{C} = 10mA,$
Fall Time	tf	_	50	ns	$I_{B1} = I_{B2} = 1.0 \text{mA}$

Note: 7. Measured under pulsed conditions. Pulse width  $\leq$  300µs. Duty cycle  $\leq$  2%.



### Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

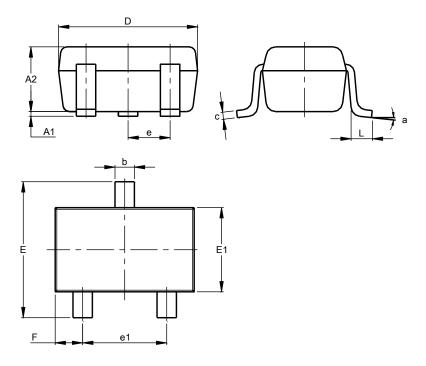




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

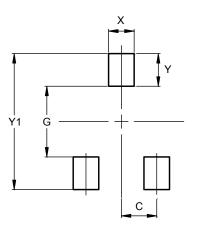
SOT323



SOT323					
Dim	Min	Max	Тур		
A1	0.00	0.10	0.05		
A2	0.90	1.00	0.95		
b	0.25	0.40	0.30		
С	0.10	0.18	0.11		
D	1.80	2.20	2.15		
Е	2.00	2.20	2.10		
E1	1.15	1.35	1.30		
е	0.650 BSC				
e1	1.20	1.40	1.30		
F	0.375	0.475	0.425		
L	0.25	0.40	0.30		
а	0°	8°			
All Dimensions in mm					

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.



 
 Dimensions
 Value (in mm)

 C
 0.650

 G
 1.300

 X
 0.470

 Y
 0.600

 Y1
 2.500

SOT323



#### **IMPORTANT NOTICE**

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

#### LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
  - 1. are intended to implant into the body, or
  - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2019, Diodes Incorporated

www.diodes.com